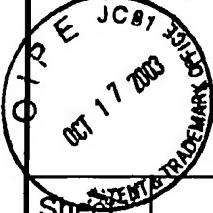


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| Application Number | 10/615,127 |
| Filing Date | July 24, 2003 |
| Confirmation Number | 8157 |
| First Named Inventor | Falster et al |
| Group Art Unit | 1765 |
| Examiner Name | Hiteshen |
| Attorney Docket No. | MEMC TP-01-2450 (3009) |

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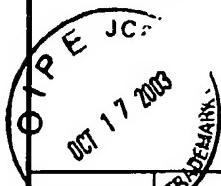
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| Group Art Unit | 1745 |
| Examiner Name | Hiteshew |

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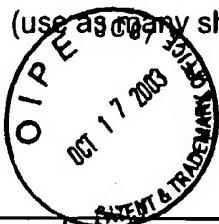
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| Group Art Unit | 1765 |
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